A theoretical study of electron drift mobility anisotropy in n-type 4H- and 6H-SiC
Velmre, Enn; **Udal, Andres** Abstracts of International Conference on Silicon Carbide and Related Materials : ICSCRM'99 : October 10-15, 1999, Research Triangle Park, North-Carolina, USA 1999 / paper no 395, 2 p
https://www.researchgate.net/publication/250338907_A_Theoretical_Study_of_Electron_Drift_Mobility_Anisotropy_in_n-Type_4H-and_6H-SiC

A theoretical study of electron drift mobility anisotropy in n-type 4H- and 6H-SiC
Velmre, Enn; **Udal, Andres** Proceedings of the International Conference on Silicon Carbide and Related Materials - 1999 (ICSCRM'99) : Research Triangle Park, North-Carolina, USA, Oct. 10-15, 1999. Vol. 1 2000 / p. 725-728

Can electrical phenomena be explained with the concept of an "electric family tree"?
Järvik, Jaan 18th International Symposium "Topical Problems in the Field of Electrical and Power Engineering". Doctoral School of Energy and Geotechnology III : Toila, Estonia, January 14-19, 2019 : [proceedings] 2019 / p. 45-46 : ill
https://www.ester.ee/record=b5183874*est

Change in the parameters of electron-irradiated 4H-SIC Schottky diodes as a function of the time during low-temperature isothermal annealing
Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja**; **Rang, Toomas** Silicon Carbide and Related Materials 2018 : 12th European Conference on Silicon Carbide and Related Materials (ECSCRM 2018) : Selected, peer reviewed papers from the European Conference on Silicon Carbide and Related Materials (ECSCRM 2018), September 2-6, 2018,Birmingham, UK 2019 / p. 734-737 https://doi.org/10.4028/www.scientific.net/MSF.963.734 Conference proceeding at Scopus Article at Scopus

Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons
Kozlovski, Vitali V.; **Korolkov, Oleg**; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja** Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 https://doi.org/10.4028/www.scientific.net/MSF.1004.231 Conference Proceedings at Scopus Article at Scopus

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC
Velmre, Enn; **Udal, Andres** 18th Nordic Semiconductor Meeting, Linköping, June 7-10, 1998 : abstracts 1998 / p. F-88: ill
https://iopscience.iop.org/article/10.1238/Physica.Topical.079a00193

Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC
Velmre, Enn; **Udal, Andres** Physica scripta 1999 / Proceedings of 18th Nordic Semiconductor Meeting, Linköping, Sweden, June 7-10, 1998, ISBN 91-87308-71-1, p. 193-197: ill https://ui.adsabs.harvard.edu/abs/1999PhST...79..193V/abstract

Electron-beam welding of high-entropy alloy and stainless steel: microstructure and mechanical properties
Sokkalingam, Rathinavelu; Mastanaiah, P.; Muthupandi, Veerappan; Sivaprasad, Katakam; **Prashanth, Konda Gokuldoss** Materials and manufacturing processes 2020 / p. 1885-1894 https://doi.org/10.1080/10426914.2020.1802045 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Fluorene- and fluorenone-based molecules as electron-transporting SAMs for photovoltaic devices
Svirskaite, Lauryna Monika; Kasparavicius, Ernestas; Steponaitis, Matas; Grzibovskis, Raitis; Franckevicius, Marius; **Katerski, Atanas**; Naujokaitis, Arnas; Karazhanov, Smagul; Gopi, Sajeesh Vadakkedath; Aizstrauts, Arturs RSC advances 2024 / p. 14973-14981 https://doi.org/10.1039/D4RA00964A

Growth of ultra-thin amorphous Al2O3 films on CoAl(1 0 0)
Rose, V.; **Podgurski, Vitali**; Costina, Ioan; Franchy, R. Surface science 2003 / p. 128-136
https://www.sciencedirect.com/science/article/pii/S0039602803008914

Low-temperature annealing of lightly doped n-4H-SiC layers after irradiation with fast electrons
Korolkov, Oleg; Kozlovski, Vitali V.; Lebedev, Alexander A.; **Sleptšuk, Natalja**; **Toompuu, Jana**; **Rang, Toomas** Semiconductors 2019 / p. 975−978 https://doi.org/10.1134/S1063782619070133 Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at WOS

Rein Munter: Vesi mäletab
Munter, Rein Tähenduse Teejuhid 2021 / Lk. 9 https://teejuhid.postimees.ee/7319813/rein-munter-vesi-maletab

Sb2S3 solar cells with TiO2 electron transporting layers synthesized by ALD and USP methods
Dedova, Tatjana; **Krautmann, Robert**; Rusu, Marin; **Katerski, Atanas**; **Krunks, Malle**; Unold, Thomas; **Spalatu, Nicolae**; **Mere, Arvo**; **Sydorenko, Jekaterina**; **Sibinski, Maciej**; **Oja Acik, Ilona** Solar energy materials and solar cells 2025 / art. 113279
https://doi.org/10.1016/j.solmat.2024.113279

The interplay of long range interactions and electron density distributions in polar and strongly correlated materials
Kristoffel, Nikolai; Pishtshev, Aleksandr; Rubin, Pavel; **Klopov, Mihhail** Journal of superconductivity and novel magnetism 2017 / p. 91-96 : ill https://doi.org/10.1007/s10948-016-3765-y Journal metrics at Scopus Article at Scopus Journal metrics at WOS Article at

WOS

UFG microstructure processing by ECAP from double electron-beam melted rare metal
Kommel, Lembit Nanomaterials by severe plastic deformation IV. Part 1 2008 / p. 349-354 : ill https://www.scientific.net/MSF.584-586.349

Valgus muudeti lõpuks aineks
Krustok, Jüri Eesti Päevaleht 1997 / 28. sept., lk. 6 https://dea.digar.ee/article/eestipaevaleht/1997/09/28/13.2

Влияние донорной примеси на характеристики электрон-фононного взаимодействия к-центров в сульфиде кадмия
Krustok, Jüri; Lõo, A.; **Piibe, Toomas** Tallinna Tehnikaülikooli Toimetised 1990 / lk. 23-29: ill

Влияние облучения низкоэнергетическими электронами в растровом электронном микроскопе на параметры полупроводниковых приборов
Meiler, Boriss; **Kropman, Daniel**; **Levtšenkova, Alla** Микроэлектроника 1987 / с. 165-169 : илл
https://www.ester.ee/record=b2147720*est

О возможности определения времени жизни фотоэлектронов и квантового выхода в поликристаллическом сульфиде кадмия
Kukk, Peeter-Enn; **Varvas, Jüri** Сборник статей по химии и химической технологии. 11 1964 / с. 237-243 : илл
https://www.ester.ee/record=b2181984*est https://digikogu.taltech.ee/et/Item/958b7e78-6cf4-425c-b75d-b028262eada8

Приближенный метод определения времени жизни неравновесных электронов в сульфиде кадмия
Varvas, Jüri; **Kukk, Peeter-Enn** Сборник статей по химии и химической технологии. 10 1964 / с. 257-266 : илл
https://www.ester.ee/record=b2181961*est https://digikogu.taltech.ee/et/Item/9569e6db-150a-42c8-bf3b-765725dfd969

Расчет показателя степени в формуле Миллера
Velmre, Enn Труды по электротехнике и автоматике : сборник статей. 11 1973 / с. 145-154 : илл
https://www.ester.ee/record=b2190624*est https://digikogu.taltech.ee/et/Item/d6e57925-e104-44e1-a218-c5b3110d9996